

### In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 CFR § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked-up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(c)(1)(ii). Any claim not accompanied by a marked-up version has not been changed relative to the immediate prior version, except that marked-up versions are not being supplied for any added claim or canceled claim.

### CLAIMS

✓  
Please cancel claims 49-54.

✓  
Please add the following new claims:

- sub  
C3
- B<sup>2</sup>
69. (New) A semiconductor construction comprising:  
a semiconductor substrate having a trench extending partially therein and  
upper surfaces adjacent the trench;  
an oxide layer formed over the upper surfaces of the semiconductor  
substrate and having an uppermost surface; and  
an insulative material filling the trench and having a portion outward of the  
trench and semiconductor substrate, the portion comprising an outermost upper  
surface elevationally above the uppermost surface of the oxide layer and  
sidewalls connecting the outermost upper surface with the oxide layer, the  
connection between the sidewalls and the outermost upper surface comprising  
curved corners, and the connection between the sidewalls and the oxide layer  
comprising curved corners extending from elevationally above the oxide layer  
downward to the uppermost surface of the oxide layer.
70. (New) The semiconductor construction of claim 69 wherein the  
insulative material comprises oxide.
71. (New) The semiconductor construction of claim 69 wherein the  
insulative material comprises a first insulative material partially filling the trench  
and a second insulative material formed over the first insulative material.

B2  
(Contd)  
Consider  
C3

72. (New) The semiconductor construction of claim 69 further comprising a polysilicon layer formed against the uppermost surface of the oxide layer and the portion of the insulative material.